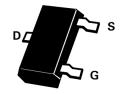


SOT23 P-CHANNEL ENHANCEMENT MODE VERTICAL DMOS FET

Features

- For automotive applications requiring specific change control (i.e. parts qualified to AEC-Q101, PPAP capable, and manufactured in IATF 16949 certified facilities), please contact us or your local Diodes representative.
- https://www.diodes.com/quality/product-definitions/



SOT23

PARTMARKING DETAIL- MX

Absolute Maximum Ratings

PARAMETER	SYMBOL	VALUE	UNIT
Drain-Source Voltage	V _{DS}	-45	V
Continuous Drain Current at T _{amb} =25°C	I _D	-90	mA
Pulsed Drain Current	I _{DM}	-1.6	А
Gate Source Voltage	V_{GS}	± 20	V
Power Dissipation at T _{amb} =25°C	P _{tot}	330	mW
Operating and Storage Temperature Range	$T_j:T_{stg}$	-55 to +150	°C

Electrical Characteristics (@ T_A = +25°C, unless otherwise specified.)

PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	CONDITIONS.	
Drain-Source Breakdown Voltage	BV _{DSS}	-45	-70		V	I_{D} =-100 μ A, V_{GS} =0 V	
Gate-Source Threshold Voltage	V _{GS(th)}	-1		-3.5	V	I_D =-1mA, V_{DS} = V_{GS}	
Gate-Body Leakage	I _{GSS}			-20	nA	V _{GS} =-15V, V _{DS} =0V	
Zero Gate Voltage Drain Current	I _{DSS}			-0.5.	μА	V _{DS} =-25V, V _{GS} =0V	
Static Drain-Source On-State Resistance (1)	R _{DS(on)}		9	14	Ω	V _{GS} =-10V,I _D =-200mA	
Forward Transconductance (1)(2)	g _{fs}		90		mS	V _{DS} =-10V,I _D =-200mA	
Input Capacitance (2)	C _{iss}		25		pF	V _{DS} =-10V, V _{GS} =0V, f=1MHz	
Turn-On Delay Time (2)(3)	t _{d(on)}			10	ns		
Rise Time (2)(3)	t _r			10	ns	V _{DD} ≈-25V, I _D =-200mA	
Turn-Off Delay Time (2)(3)	t _{d(off)}			10	ns		
Fall Time (2)(3)	t _f			10	ns		

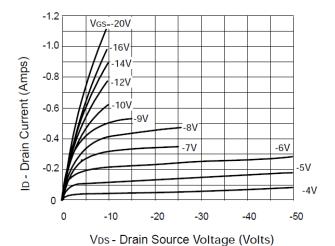
⁽¹⁾ Measured under pulsed conditions. Width=300 μ s. Duty cycle≤2% (2) Sample test.

Spice parameter data is available upon request for this device

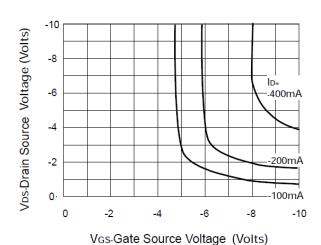
⁽³⁾ Switching times measured with 50Ω source impedance and <5ns rise time on a pulse generator



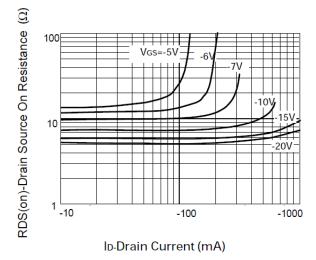
Typical Characteristics



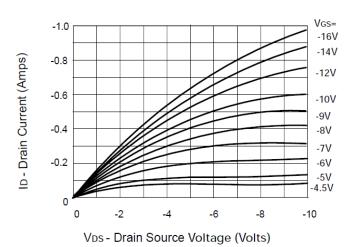
Output Characteristics



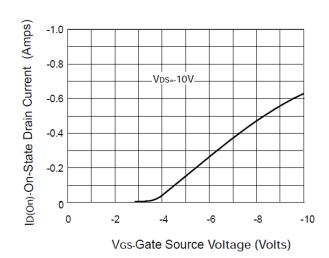
Voltage Saturation Characteristics



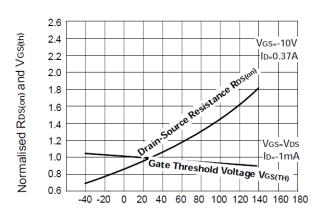
On-resistance vs Drain Current



Saturation Characteristics



Transfer Characteristics

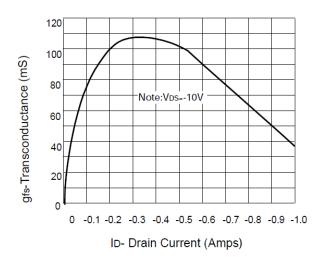


Junction Temperature (°C)

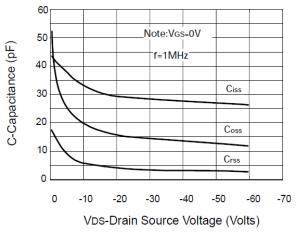
Normalised RDS(on) and VGS(th) vs Temperature



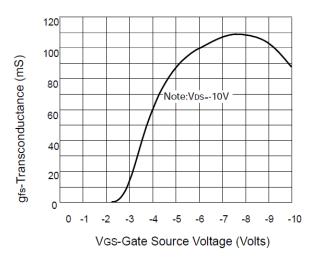
Typical Characteristics (continued)



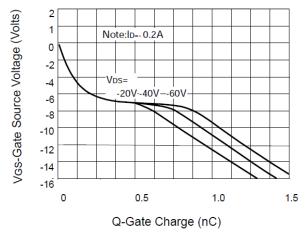
Transconductance v drain current



Capacitance v drain-source voltage



Transconductance v gate-source voltage



Gate charge v gate-source voltage



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